

STTH112

High voltage ultrafast rectifier

Main product characteristics

$I_{F(AV)}$	1 A
V_{RRM}	1200 V
$T_j(max)$	175° C
$V_F(max)$	1.65 V

Features and benefits

- Low forward voltage drop
- High reliability
- High surge current capability
- Soft switching for reduced EMI disturbances
- Planar technology

Description

The STTH112, which is using ultrafast high voltage planar technology, is specially suited for free-wheeling, clamping, snubbing, demagnetization in power supplies and other power switching applications

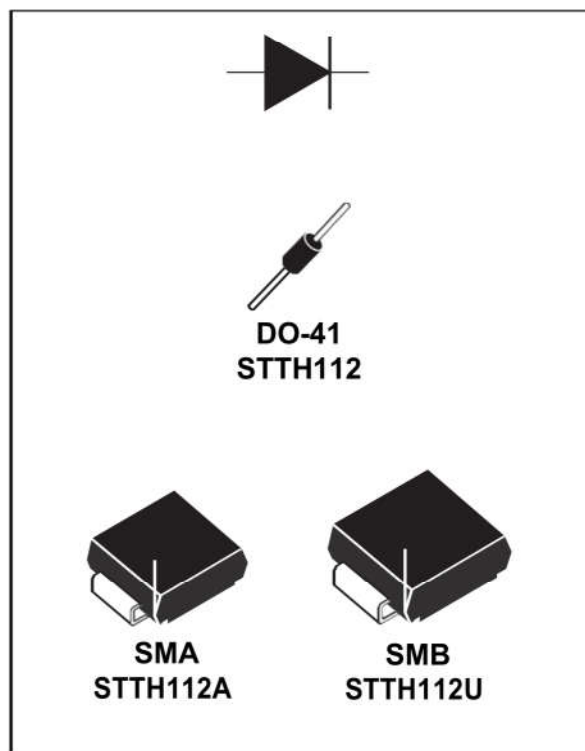


Table 1. Absolute ratings (limiting values)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			1200	V
V _(RMS)	RMS voltage			850	V
I _{F(AV)}	Average forward current	TI = 85° C δ = 0.5	DO-41	1	A
		TI = 115° C δ = 0.5	SMA		
		TI = 125° C δ = 0.5	SMB		
I _{FSM}	Forward surge current t = 8.3 ms		DO-41	20	A
			SMA	18	
			SMB		
T _{stg}	Storage temperature range			- 50 + 175	°C
T _j	Maximum operating junction temperature			+ 175	°C

2. Electrical characteristics

Table 2. Thermal parameters

Symbol	Parameter			Value	Unit
$R_{th(j-l)}$	Junction to lead	L = 10 mm	DO-41	45	$^{\circ}\text{C/W}$
			SMA	30	
			SMB	25	
$R_{th(j-a)}$	Junction to ambient	L = 10 mm	DO-41	110	

Table 3. Static electrical characteristics

Symbol	Parameter	Tests conditions	Min.	Typ.	Max.	Unit
I_R	Reverse leakage current	$V_R = 1200\text{V}$	$T_j = 25^{\circ}\text{C}$		5	μA
			$T_j = 125^{\circ}\text{C}$		50	
V_F	Forward voltage drop	$I_F = 1\text{A}$	$T_j = 25^{\circ}\text{C}$		1.9	V
			$T_j = 125^{\circ}\text{C}$	1.17	1.65	
			$T_j = 150^{\circ}\text{C}$	1.10	1.55	

Table 4. Dynamic electrical characteristics

Symbol	Parameter	Tests conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5\text{A}$ $I_{rr} = 0.25\text{A}$ $I_R = 1\text{A}$	$T_j = 25^{\circ}\text{C}$		75	ns
t_{fr}	Forward recovery time	$I_F = 1\text{A}$ $dI_F/dt = 50\text{A}/\mu\text{s}$	$T_j = 25^{\circ}\text{C}$		500	ns
V_{FP}	Forward recovery voltage	$V_{FR} = 1.1 \times V_{Fmax}$			30	V

Figure 1. Conduction losses versus average current

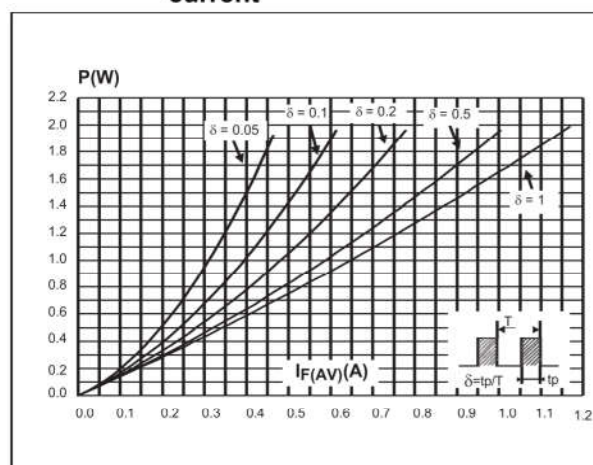


Figure 2. Forward voltage drop versus forward current.

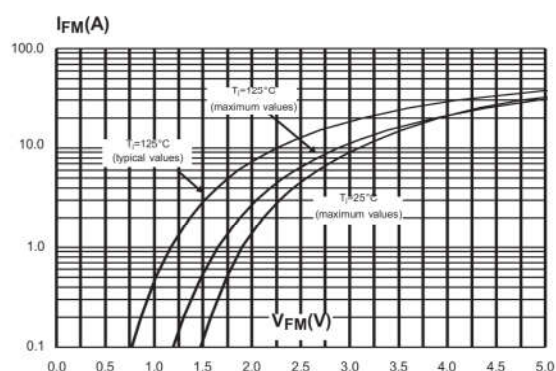


Figure 3. Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4, $L_{\text{leads}} = 10\text{mm}$) (DO-41).

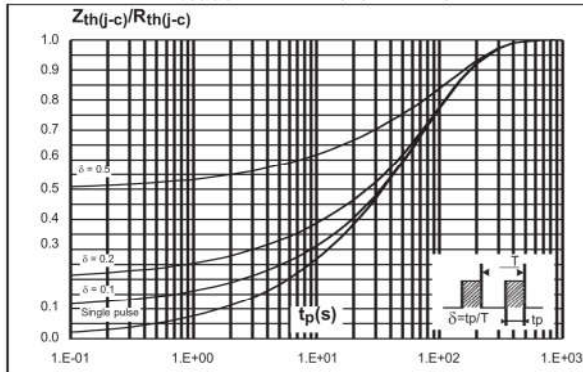


Figure 4. Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4) (SMA).

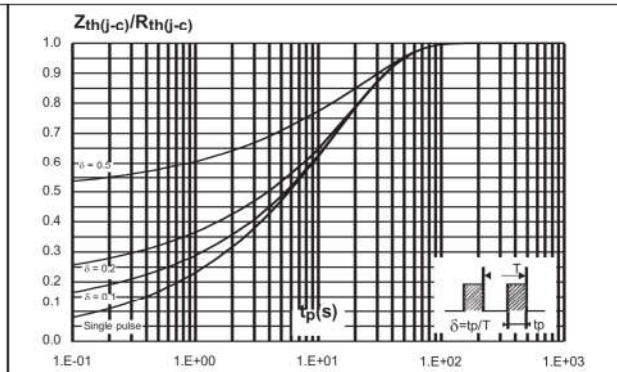


Figure 5. Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4)(SMB).

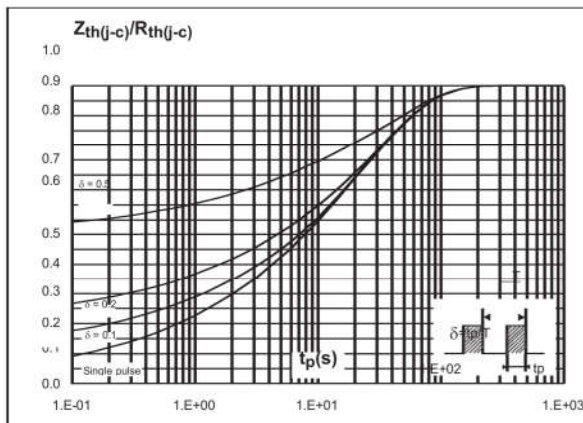


Figure 6. Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: 35 μm) (DO-41, SMB).

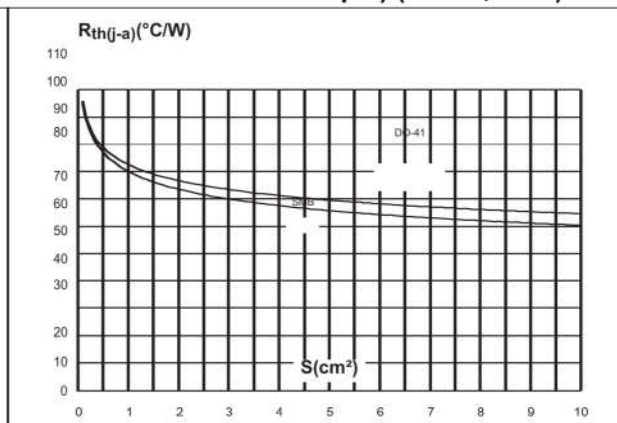
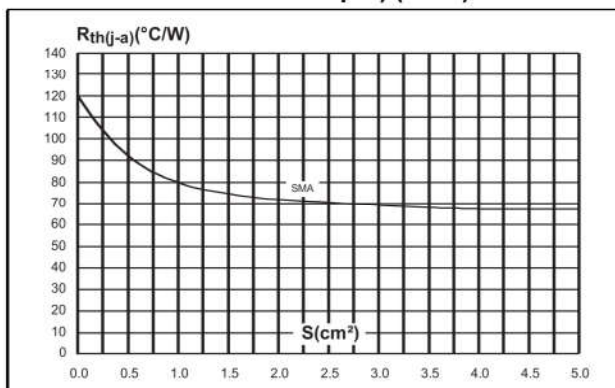


Figure 7. Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: 35 μm) (SMA).



1 Package mechanical data

Epoxy meets UL 94, V0

Table 5. SMA dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.094
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.40	0.006	0.016
D	2.25	2.90	0.089	0.114
E	4.80	5.35	0.189	0.211
E1	3.95	4.60	0.156	0.181
L	0.75	1.50	0.030	0.059

Figure 8. Footprint (dimensions in mm)

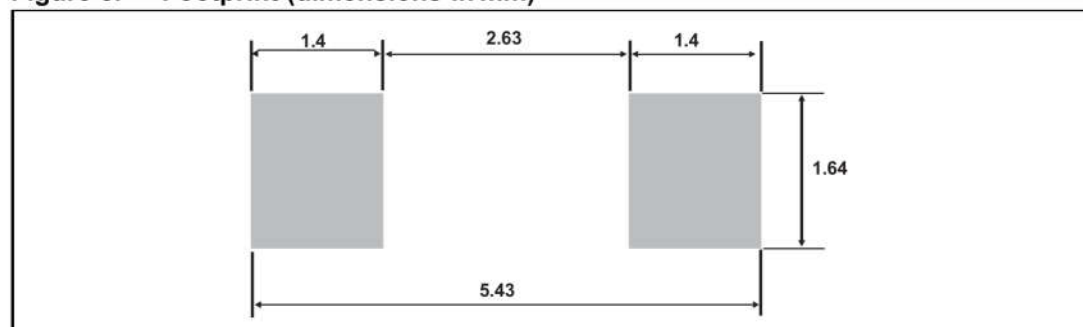


Table 6. SMB dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.40	0.006	0.016
D	3.30	3.95	0.130	0.156
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
L	0.75	1.50	0.030	0.059

Figure 9. Footprint (dimensions in mm)

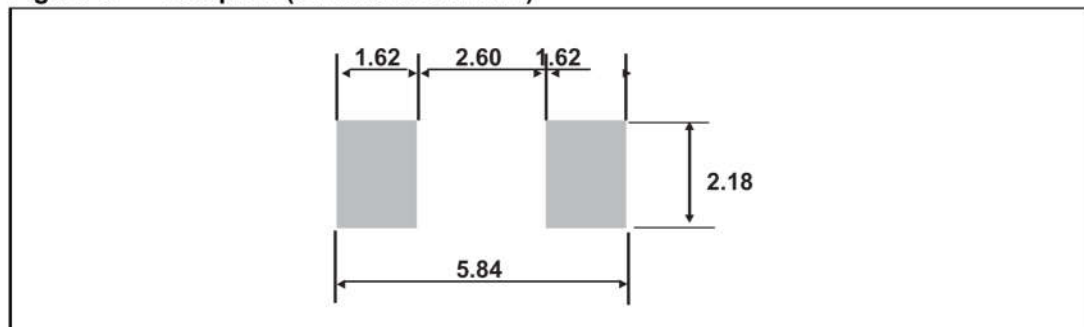


Table 7. DO-41 dimensions

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
C	28		1.102	
D	0.712	0.863	0.028	0.034